

RJK1536DPN

N-Channel Power MOSFET High-Speed Switching Use

REJ03G1594-0200 Rev.2.00 Mar 11, 2008

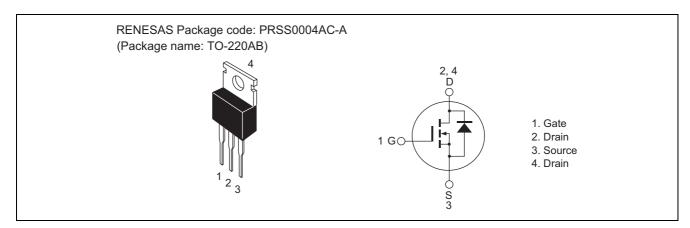
Features

• V_{DSS}: 150 V

• $R_{DS(on)}$: 30 m Ω (Max)

• I_D: 50 A

Outline



Application

• Motor control, Solenoid control, DC-DC converter, etc.

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	150	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I _D	50	А
Drain peak current	I _{D (pulse)}	100	А
Body-drain diode reverse drain current	I _{DR}	50	А
Body-drain diode reverse drain peak current	I _{DR (pulse)}	100	А
Avalanche current	I _{AP} Note2	25	А
Channel dissipation	Pch Note1	125	W
Channel to case thermal impedance	θch-c	1.0	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. Value at Tc = 25°C

2. STch = 25°C, Tch \leq 150°C, L = 100 μH

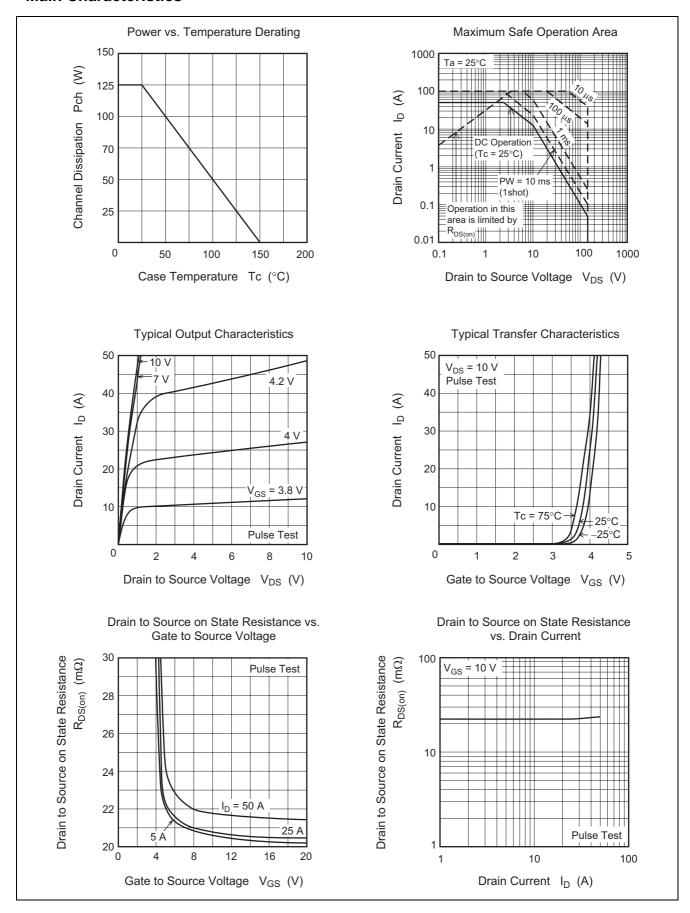
Electrical Characteristics

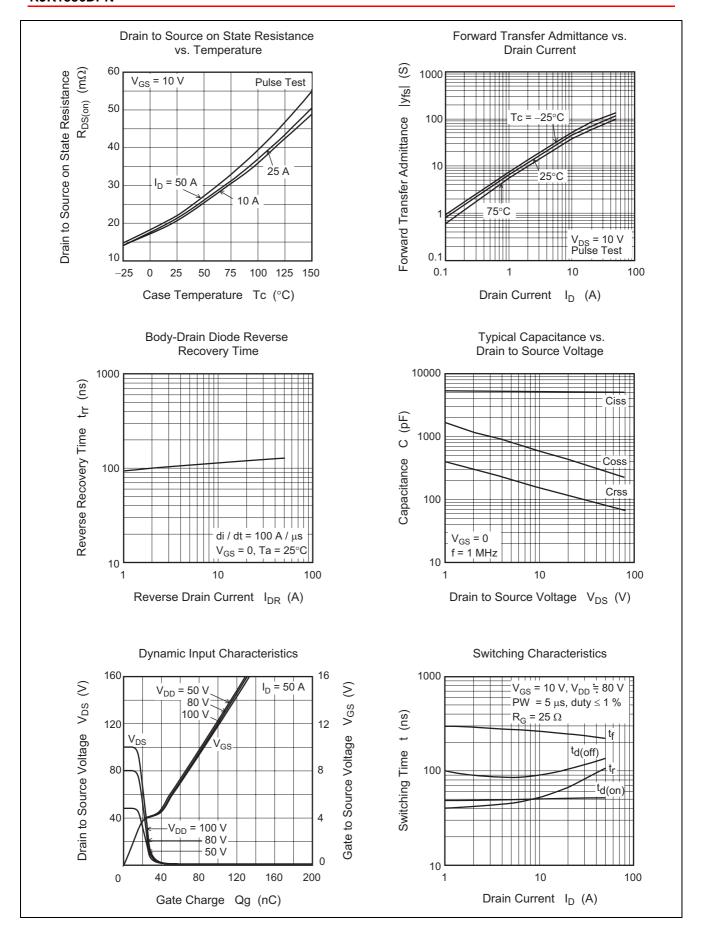
 $(Ta = 25^{\circ}C)$

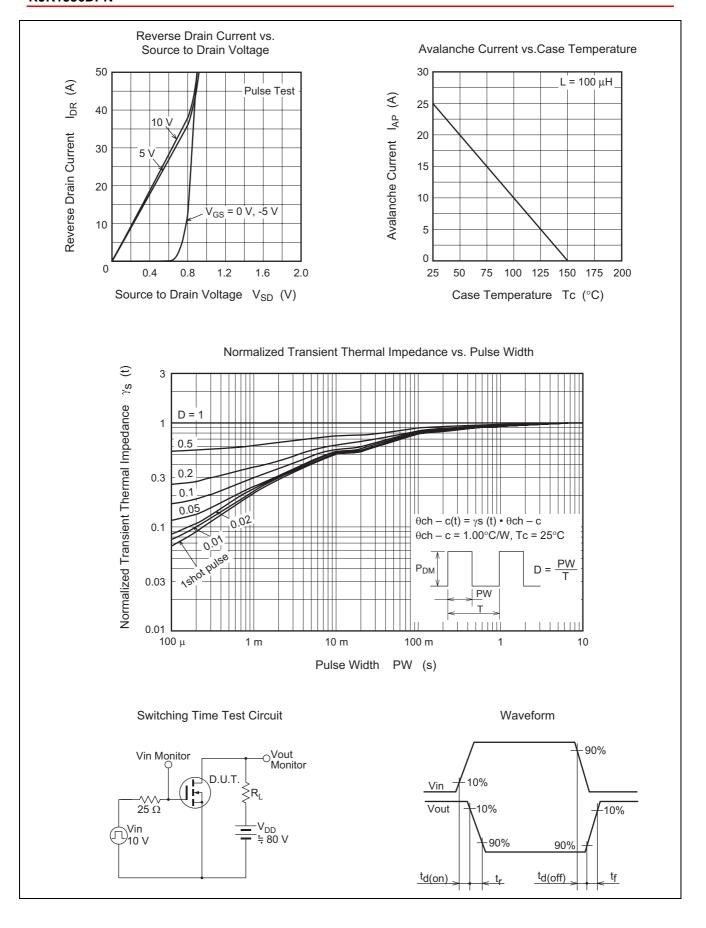
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	150	_	_	V	$I_D = 1 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	100	μΑ	$V_{DS} = 150 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	3.0	4.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}^{\text{Note3}}$
Static drain to source on state voltage	$V_{DS(on)}$	_	0.60	0.75	V	$I_D = 25 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
Static drain to source on state	R _{DS(on)}	_	24	30	mΩ	$I_D = 25 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
resistance						
Input capacitance	Ciss	_	5000		pF	V _{DS} = 10 V
Output capacitance	Coss	_	560		pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	165	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	50	_	ns	V _{DD} = 80 V
Rise time	t _r	_	75	_	ns	I _D = 25 A
Turn-off delay time	t _{d(off)}	_	250	_	ns	$V_{GS} = 10 \text{ V}$
Fall time	t _f	_	100	_	ns	$R_G = 25 \Omega$
Body-drain diode forward voltage	V_{DF}	_	0.9	1.5	V	I _F = 25 A, V _{GS} = 0
Body-drain diode reverse recovery time	t _{rr}	_	130	_	ns	$I_F = 50 \text{ A}, V_{GS} = 0$
						$di_F/dt = 100 A/\mu s$

Notes: 3. Pulse test

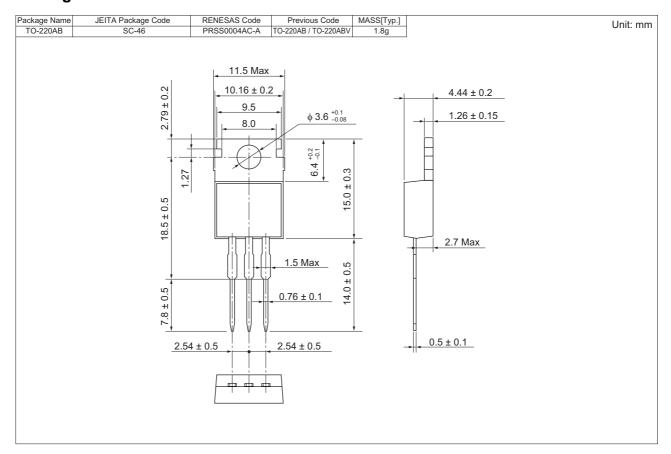
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK1536DPN-00-02	500 pcs	Box (Sack)

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